

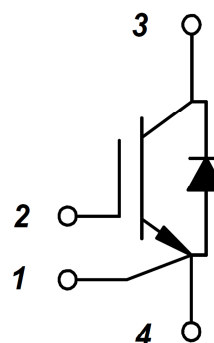
PRODUCT FEATURES

- ☐ IGBT chip in trench FS-technology
- ☐ Low switching losses
- ☐ $V_{CE(sat)}$ with positive temperature coefficient
- ☐ Fast switching and short tail current
- ☐ Free wheeling diodes with fast and soft reverse recovery
- ☐ Popular SOT-227 Package



APPLICATIONS

- ☐ High frequency switching application
- ☐ Medical applications
- ☐ Motion/servo control
- ☐ UPS systems



IGBT-inverter

ABSOLUTE MAXIMUM RATINGS

 $T_C = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J = 25^{\circ}\text{C}$	1200	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C = 25^{\circ}\text{C}$	100	A
		$T_C = 80^{\circ}\text{C}$	75	
I_{CM}	Repetitive Peak Collector Current	$t_p = 1\text{ms}$	150	
P_{tot}	Power Dissipation Per IGBT		410	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS

 $T_C = 25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J = 25^{\circ}\text{C}$	1200	V
$I_{F(AV)}$	Average Forward Current	$T_C = 25^{\circ}\text{C}$	60	A
I_{FRM}	Repetitive Peak Forward Current	$t_p = 1\text{ms}$	120	
I^2t		$T_J = 125^{\circ}\text{C}$, $t = 10\text{ms}$, $V_R = 0\text{V}$	1012	A^2S

IGBT-inverter

ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit	
V _{GE(th)}	Gate Emitter Threshold Voltage	V _{CE} =V _{GE} , I _C =3mA	5.0	5.8	6.5	V	
V _{CE(sat)}	Collector Emitter Saturation Voltage	I _C =75A, V _{GE} =15V, T _J =25℃		2.2	2.5		
		I _C =75A, V _{GE} =15V, T _J =125℃		2.5			
I _{CES}	Collector Leakage Current	V _{CE} =1200V, V _{GE} =0V, T _J =25℃			100	mA	
		V _{CE} =1200V, V _{GE} =0V, T _J =125℃			1	mA	
I _{GES}	Gate Leakage Current	V _{CE} =0V, V _{GE} =±15V, T _J =125℃	-400		400	nA	
R _{gint}	Integrated Gate Resistor			0		Ω	
Q _g	Gate Charge	V _{CE} =600V, I _C =75A , V _{GE} =15V		0.4		μC	
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f =1MHz		9.4		nF	
C _{res}	Reverse Transfer Capacitance			160		pF	
t _{d(on)}	Turn on Delay Time	V _{CC} =600V, I _C =75A R _G =15Ω, V _{GE} =±15V, Inductive Load	T _J =25℃	80		ns	
			T _J =125℃	90		ns	
t _r	Rise Time		T _J =25℃	45		ns	
			T _J =125℃	50		ns	
t _{d(off)}	Turn off Delay Time		T _J =25℃	360		ns	
			T _J =125℃	400		ns	
t _f	Fall Time		T _J =25℃	50		ns	
			T _J =125℃	60		ns	
E _{on}	Turn on Energy	V _{CC} =600V, I _C =75A R _G =15Ω, V _{GE} =±15V, Inductive Load	T _J =25℃	4.8		mJ	
			T _J =125℃	7.5		mJ	
E _{off}	Turn off Energy		T _J =25℃	3.2		mJ	
			T _J =125℃	3.8		mJ	
I _{sc}	Short Circuit Current		tpsc≤10μS , V _{GE} =15V T _J =125℃, V _{CC} =600V		300		A
R _{thJC}	Junction to Case Thermal Resistance （Per IGBT）				0.3	K /W	

Diode-inverter

ELECTRICAL CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V _F	Forward Voltage	I _F =60A , V _{GE} =0V, T _J =25℃		2.4	2.8	V
		I _F =60A , V _{GE} =0V, T _J =125℃		2.0		
t _{rr}	Reverse Recovery Time	I _F =60A , V _R =600V dI _F /dt=-1000A/μs T _J =125℃		150		ns
I _{RRM}	Max. Reverse Recovery Current			68		A
Q _{RR}	Reverse Recovery Charge			4.8		μC
E _{rec}	Reverse Recovery Energy			2.2		mJ
R _{thJCD}	Junction to Case Thermal Resistance （ Per Diode）				0.7	K /W

MODULE CHARACTERISTICS

 $T_C = 25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter/Test Conditions		Values	Unit
T_{Jmax}	Max. Junction Temperature		150	$^\circ\text{C}$
T_{Jop}	Operating Temperature		-40~125	
T_{stg}	Storage Temperature		-40~125	
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	3000	V
Torque	to heatsink	Recommended (M4)	0.7~1.1	Nm
	to terminal	Recommended (M4)	0.7~1.1	Nm
Weight			26.5	g

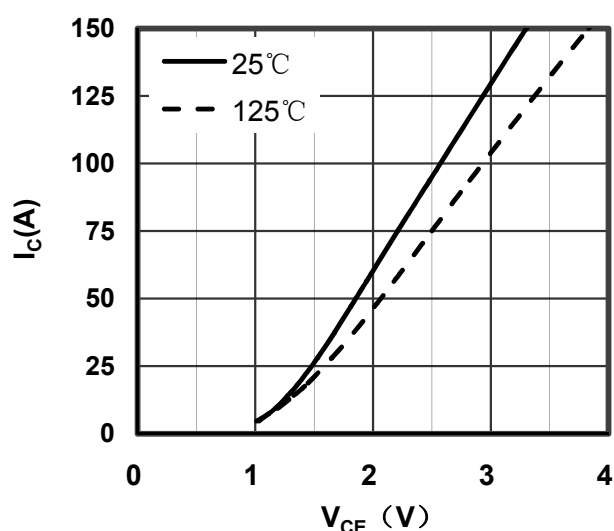


Figure 1. Typical Output Characteristics IGBT-inverter

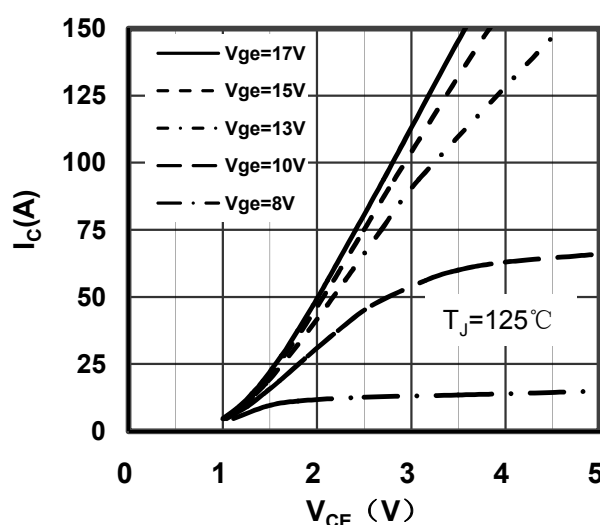


Figure 2. Typical Output Characteristics IGBT-inverter

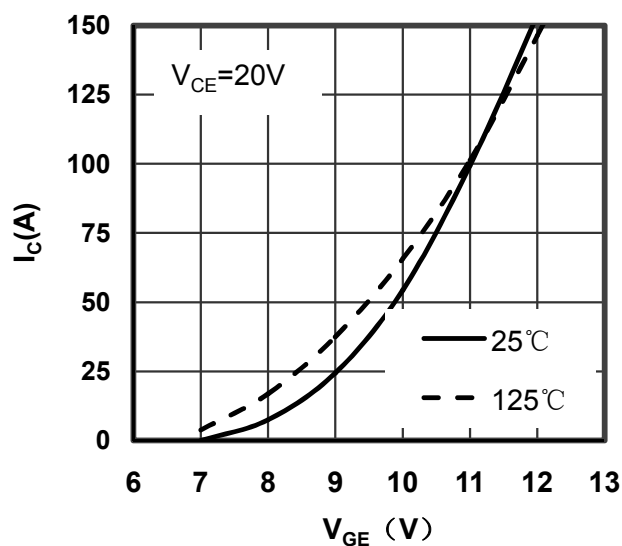


Figure 3. Typical Transfer characteristics IGBT-inverter

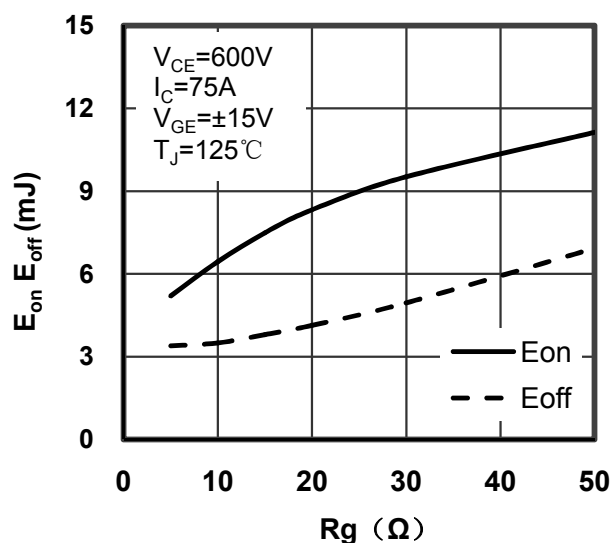


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

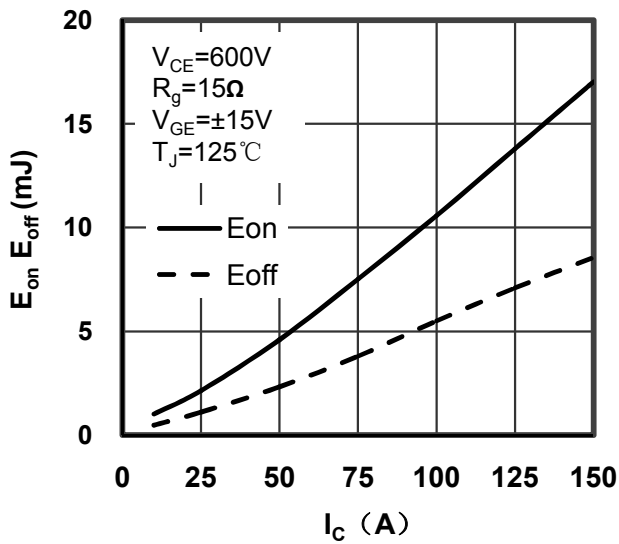


Figure 5. Switching Energy vs Collector Current IGBT-inverter

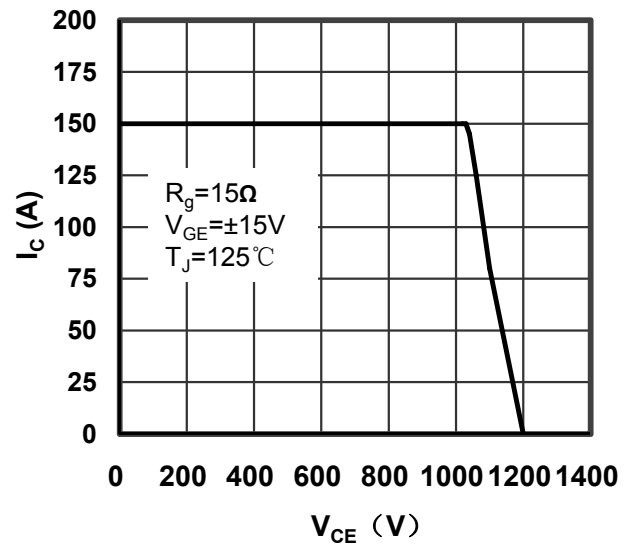


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

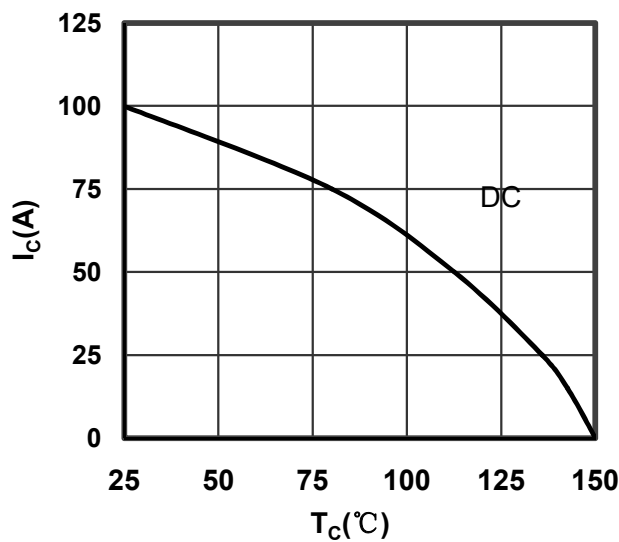


Figure 7. Collector Current vs Case temperature IGBT -inverter

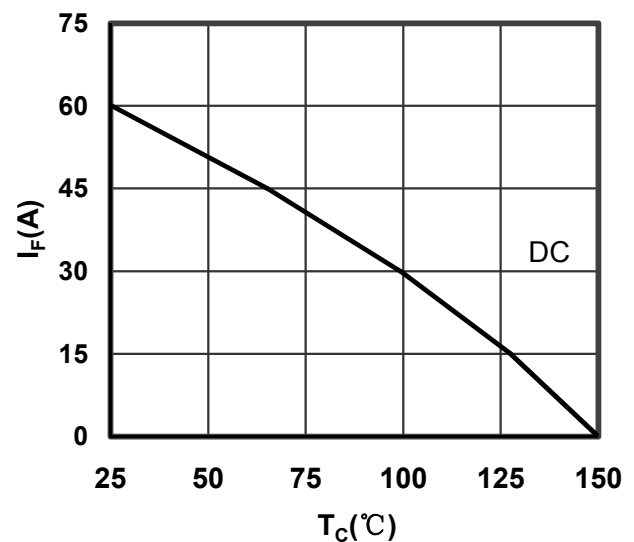


Figure 8. Forward current vs Case temperature Diode -inverter

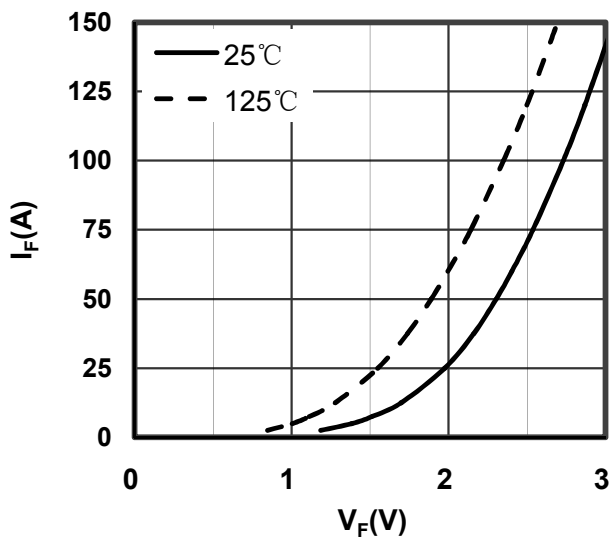


Figure 9. Diode Forward Characteristics Diode -inverter

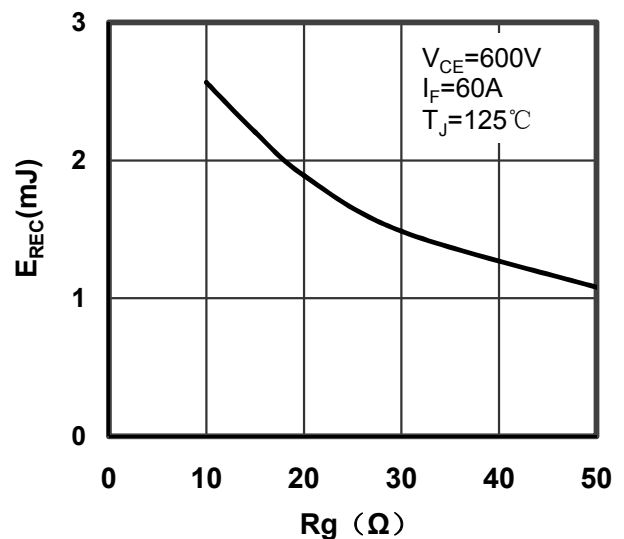


Figure 10. Switching Energy vs Gate Resistor Diode -inverter

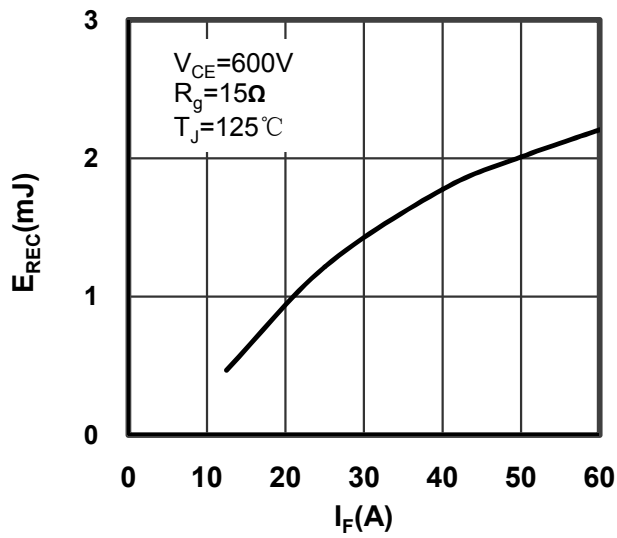


Figure 11. Switching Energy vs Forward Current Diode-inverter

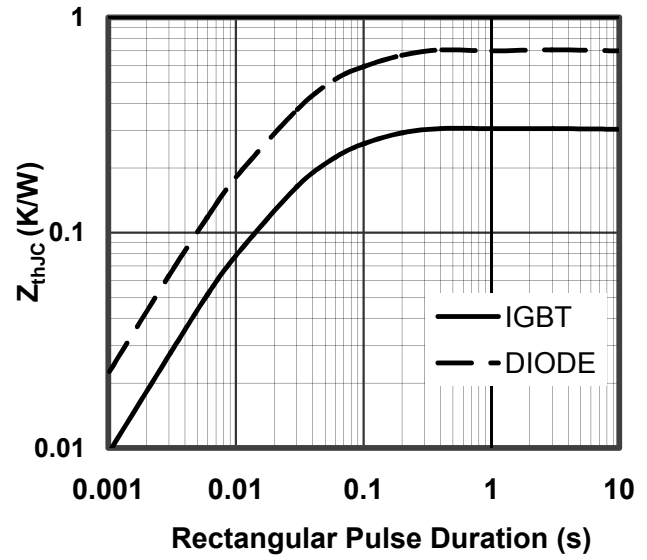
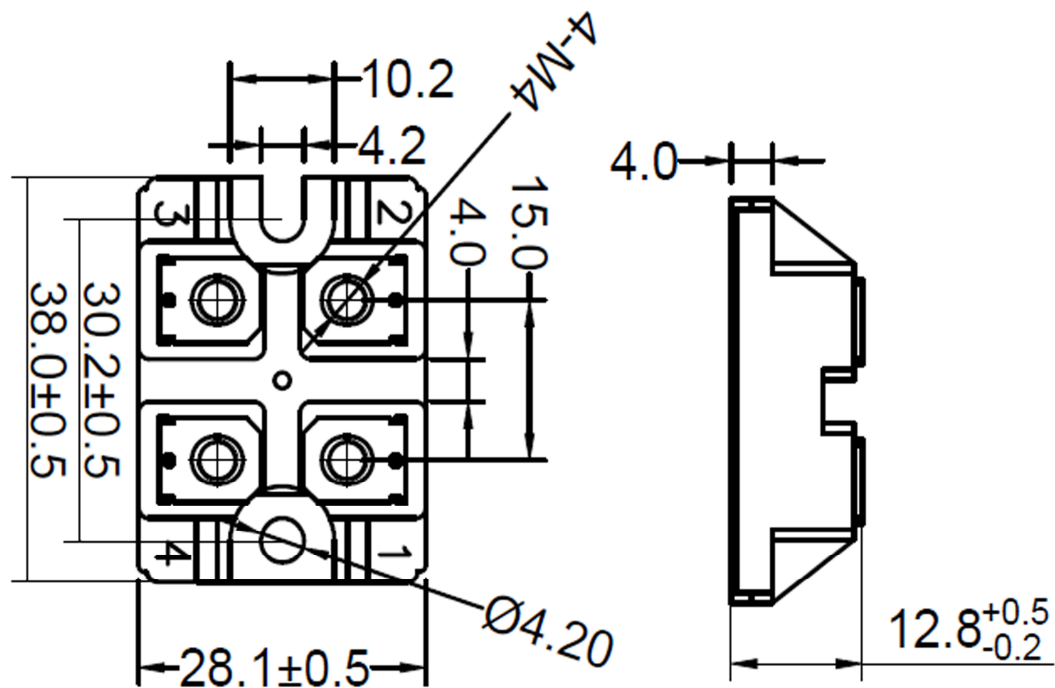


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter



Dimensions in (mm)
Figure 13. Package Outline